SCH1331

Power MOSFET –12V, 84mΩ, –3A, Single P-Channel

This Low-profile High-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

Features

- Low On-Resistance
- High speed switching
- 1.8V drive
- Low capacitance
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

Typical Applications

- Battery Switch
- Load Switch
- DC/DC Converter
- Lens Motor Driver

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

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Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-12	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	۱D	-3	А
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	-12	A
Power Dissipation When mounted on ceramic substrate (900mm ² × 0.8mm)	PD	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2 : This product is designed to "ESD immunity < 200V*", so please take care when handling. *Machine Model

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² \times 0.8mm)	$R_{\theta J A}$	125	°C/W

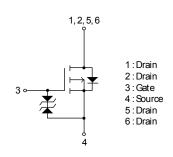


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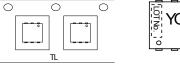
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VDSS	R _{DS} (on) Max	ID Max
-12V	84mΩ@ –4.5V	
	126mΩ@ –2.5V	-3A
	230mΩ@ −1.8V	

ELECTRICAL CONNECTION P-Channel



PACKING TYPE : TL MARKING



ORDERING INFORMATION See detailed ordering and shipping

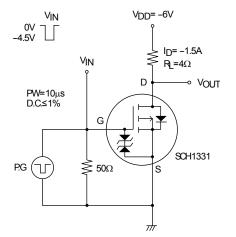
information on page 5 of this data sheet.

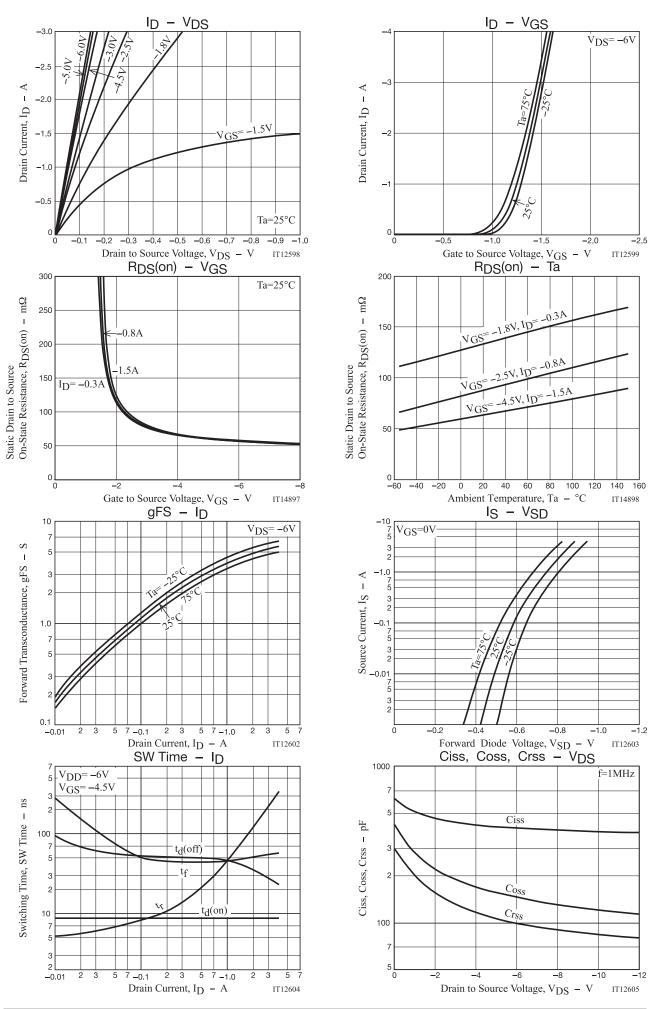
Deremeter	Cumbol	Symbol Conditions	Value			l linit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.3	V
Forward Transconductance	9FS	V _{DS} =-6V, I _D =-1.5A	2.7	4.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	ID=-1.5A, VGS=-4.5V		64	84	mΩ
	R _{DS} (on)2	ID=-0.8A, VGS=-2.5V		90	126	mΩ
	R _{DS} (on)3	ID=-0.3A, VGS=-1.8V		135	230	mΩ
Input Capacitance	Ciss	V _{DS} =–6V, f=1MHz		405		pF
Output Capacitance	Coss			145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t _d (on)			8.8		ns
Rise Time	tr			80		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		41		ns
Fall Time	tf			50		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-2.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.6		nC
Forward Diode Voltage	V _{SD}	IS=-2.5A, VGS=0V		-0.82	-1.2	V

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

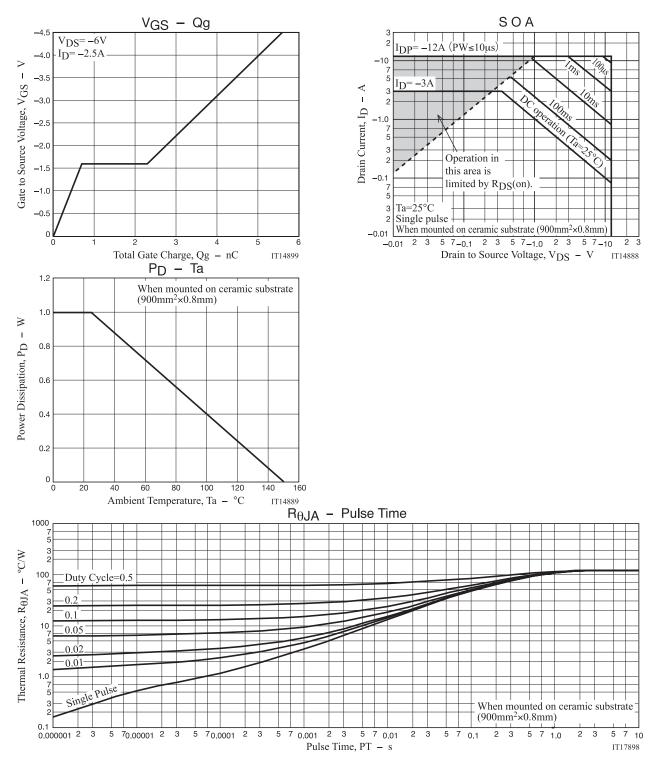
Switching Time Test Circuit





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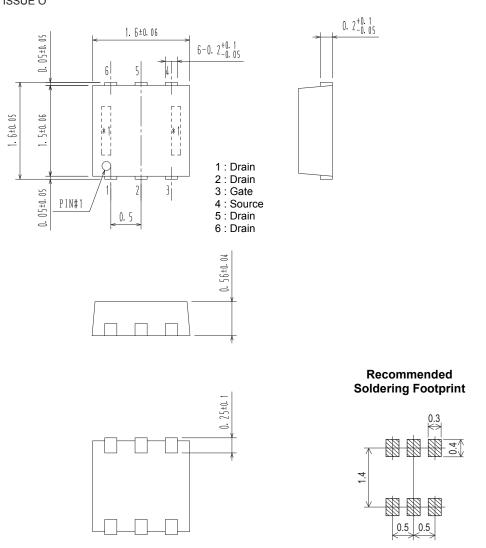
SCH1331



PACKAGE DIMENSIONS

unit : mm

SOT-563 / SCH6 CASE 463AB ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
SCH1331-TL-H	YG	SOT-563 / SCH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel	
SCH1331-TL-W				

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the SCH1331 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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